

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- **ESD Protected Up To 2KV**
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

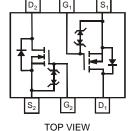
Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)









TOP VIEW

BOTTOM VIEW

Maximum Ratings @T_A = 25°C unless otherwise specified

Char	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage			V_{GSS}	±6	V
Continuous Drain Current (Note 3)	Steady State	T _A = 25°C T _A = 85°C	I _D	1.38 0.89	А
Pulsed Drain Current (Note 4)	I _{DM}	3	Α		

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 3)	P _D	530	mW
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 3)	R _{0JA}	235	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

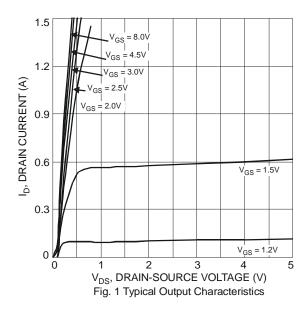


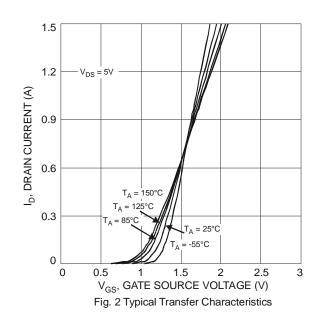
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage		20	-	1	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	100	nΑ	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	-	±1.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 5)						•
Gate Threshold Voltage	V _{GS(th)}	0.5	-	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
			0.3	0.45	Ω	$V_{GS} = 4.5V, I_D = 600mA$
			0.4	0.6		$V_{GS} = 2.5V, I_D = 500mA$
Static Drain-Source On-Resistance	R _{DS (ON)}	-	0.5	0.75		$V_{GS} = 1.8V, I_D = 350mA$
	, ,		-	9		V _{GS} = 1.7V, I _D = 140mA
			-	10		V _{GS} = 1.5V, I _D = 100mA
Forward Transfer Admittance	Y _{fs}	-	1.4	-	S	$V_{DS} = 10V, I_D = 400mA$
Diode Forward Voltage	V _{SD}		0.7	1.2	V	V _{GS} = 0V, I _S = 150mA
DYNAMIC CHARACTERISTICS (Note 6)	-					
Input Capacitance	C _{iss}	-	60.67	-	pF	101/11/101/
Output Capacitance	Coss	-	9.68	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	-	5.37	-	pF	-1 = 1.0MHZ
Total Gate Charge	Qq	-	736.6	-	рC	4.51/.1/
Gate-Source Charge	Q _{qs}	-	93.6	-	рC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q _{ad}	-	116.6	-	рС	$I_D = 250 \text{mA}$
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns	.,,
Turn-On Rise Time	t _r	-	7.4	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(off)}	-	26.7	-	ns	$R_L = 47\Omega$, $R_G = 10\Omega$,
Turn-Off Fall Time	t _f	-	12.3	-	ns	$I_D = 200 \text{mA}$

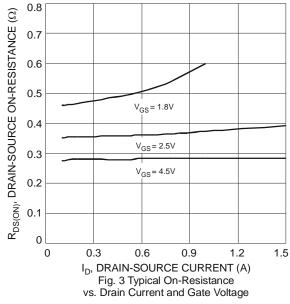
Notes: 5. Short duration pulse test used to minimize self-heating effect.

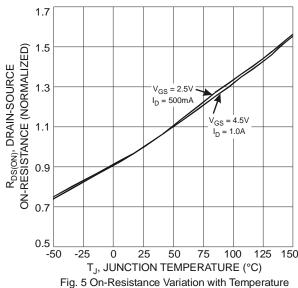
6. Guaranteed by design. Not subject to production testing.











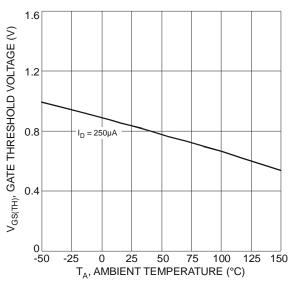


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

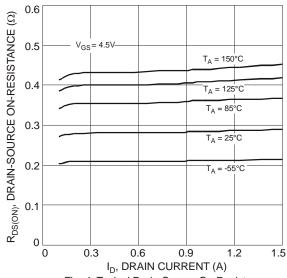


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

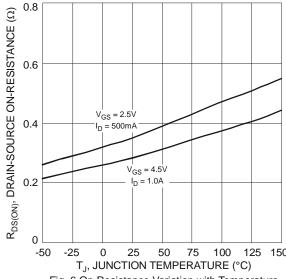


Fig. 6 On-Resistance Variation with Temperature

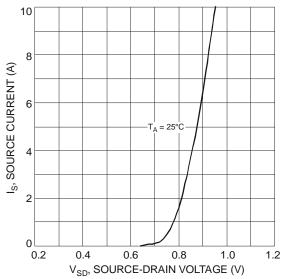
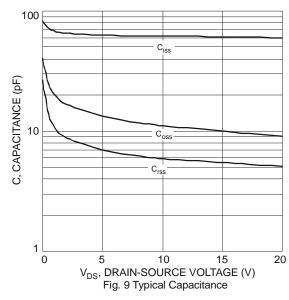


Fig. 8 Diode Forward Voltage vs. Current





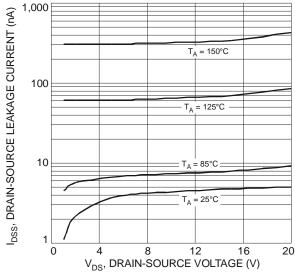
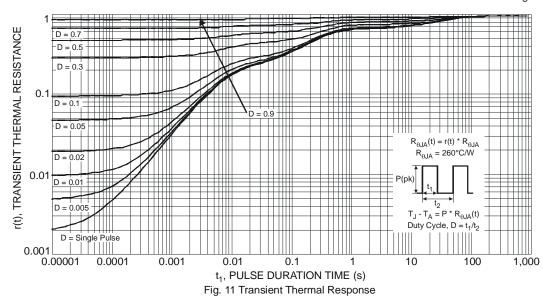


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

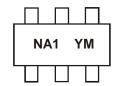


Ordering Information (Note 7)

Part Number	Case	Packaging
DMG1024UV-7	SOT-563	3000 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



NA1 = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: W = 2009)

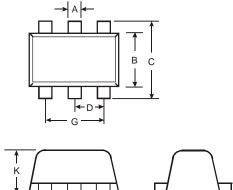
M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		X		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

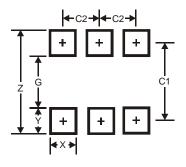


Package Outline Dimensions



SOT-563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
K	0.55	0.60	0.60			
L	0.10	0.30	0.20			
M	0.10	0.18	0.11			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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